

FORM PTO-1449 US DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Atty. Docket No. 80236DPCW Customer No. 01333		Serial No. To Be Assigned		
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		Filing Date Herewith		Group To Be Assigned		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)						
U.S. PATENT DOCUMENTS						
Examiner Initial*	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>[Signature]</i>	5,738,800	14Apr1998	Hosali et al.	216	99	
<i>[Signature]</i>	5,759,917	02Jun1998	Grover et al.	438	690	
<i>[Signature]</i>	6,299,659 B1	09Oct2001	Kido et al.	51	309	
<i>[Signature]</i>	6,042,741	28Mar2000	Hosali et al.	252	79.1	
<i>[Signature]</i>	6,132,637	17Oct2000	Hosali et al.	252	79.1	
<i>[Signature]</i>	6,218,305 B1	17Apr2001	Hosali et al.	438	691	
<i>[Signature]</i>	6,027,554	22Feb2000	Kodama et al.	106	3	
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<i>[Signature]</i>	5,575,885	19Nov1996	Hirabayashi et al.	156	626.1	
<i>[Signature]</i>	5,733,819	31Mar1998	Kodama et al.	438	692	
<i>[Signature]</i>	6,410,444	25Jun2002	Kido et al.	438	693	
<i>[Signature]</i>	6,436,835	20Aug2002	Kido et al.	438	693	
FOREIGN PATENT DOCUMENTS						
Examiner Initial*	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	WO99/43761	01Sep1999	PCT (See EP1061111A1 for english equivalent)			X
<i>[Signature]</i>	EP 1 061 111 A1	20Dec2000	EPO (Eng. Eqv. WO99/43761)			X
<i>[Signature]</i>	0 786 504 A2	30Jul1997	EP	C09G	1/02	X
<i>[Signature]</i>	0 846 740 A1	10Jun1998	EP	C09G	1/02	X
<i>[Signature]</i>	0 853 335 A2	15Jul1998	EP	H01L	21/3105	X
<i>[Signature]</i>	WO 99/53532	21Oct1999	PCT	H01L	21/00	X
<i>[Signature]</i>	0 659 858 A2	28Jun1995	EP	C09G	1/02	X
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)						
<i>[Signature]</i>	Chemical Mechanical Planarization of Microelectronic Materials, "8.1.2 Shallow Trench Isolation"; by J. M. Steigerwald, S. P. Muraka, and R. J. Gutman; ISBN 0-471-13827-4 (Jon Wiley & Son, Inc. 1997), pages 273-274.					
<i>[Signature]</i>	A High Oxide:Nitride Selectivity CMP Slurry For Shallow Trench Isolation; by Sharath Hosali and Ray Lavoie; Electrochemical Society Proceedings, Volume 98-7, pages 218-234.					
<i>[Signature]</i>	Application of Ceria-Based High Selectivity Slurry to STI CMP for Sub 0.18 μ m CMOS Technologies; by Ki-Sik Choi, Sang-Ick Lee, Chang-Il Kim, Chul-Woo Nam, Sam-Dong Kim, and Chung-Tae Kim; CMP-MIC Conference, February 11-12, 1999, pages 307-313.					
<i>[Signature]</i>	A Production-Proven Shallow Trench Isolation (STI) Solution Using Novel CMP Concepts; by Raymond R. Jin, Jeffery David, Bob Abbassi, Tom Osterheld, and Fritz Redeker; CMP-MIC Conference, February 11-12, 1999, pages 314-321.					
<i>[Signature]</i>	A Wide Margin CMP and Clean Process For Shallow Trench Isolation Applications; by Brad Withers, Eugene Zhao, Rahul Jairath; CMP-MIC Conference, February 19-20, 1998, pages 319-327.					
<i>[Signature]</i>	Planarization Process and Consumable Development For Shallow Trench Isolation; by Sharath D. Hosali, et al.; CMP-MIC Conference, February 13-14, 1997, pages 52-57.					
<i>[Signature]</i>	Pattern Dependence And Planarization Using Silica Or Ceria Slurries For Shallow Trench Isolation; by D. R. Evans, et al.; CMP-MIC Conference, February 19-20, 1998, pages 347-350.					
<i>[Signature]</i>	A Two-Step CMP-RIE Planarization Sequence For Advanced Trench Isolation Process; by Konstantin Smekalin; CMP-MIC Conference, February 13-14, 1997, pages 21-28.					
<i>[Signature]</i>	Raising Oxide:Nitride Selectivity To Aid In The CMP Of Shallow Trench Isolation Type Applications; by C.R. Mills, et al.; CMP-MIC Conference, February 13-14, 1997, pages 179-185.					
EXAMINER			DATE CONSIDERED			
<i>[Signature]</i>			11/27/05			

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.